

NE5550234-EV04-A

Evaluation Board

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- Circuit Schematic and Assembly Drawing

Circuit Description

The NE5550234A-EV04-A is an evaluation circuit board for Renesas' LDMOS power FET, NE5550234 optimized for the performance at 460MHz. The circuit board is RoHS compliant.

Matching and Bias Circuits

Refer to the schematic and assembly drawing in the two last pages for the component designation and location.

The input matching circuit consists of two sections of LC low pass network. At output two sections of transmission line, TL1 and TL2, in combination with inductor L3, provide the required serial components for impedance transformation. The electrical lengths of the transmission lines labeled on the schematic are estimated and for reference only. Some bench tuning on the actual circuit board is usually required to achieve optimal performance. For applications where there is a constraint on the board space, serial inductors, instead of transmission lines, can be used for the matching circuits. Low loss inductors should be selected to maintain good efficiency of the PA circuit. The resistor, R3(=2.4ohm) at input is used to improve the stability margin. The gain is reduced by about 1-2dB when R3 is used.

LDMOSFETs essentially draw no gate current under normal operation conditions. Therefore a large value resistor, in the order of k Ω , can be used for the bias at gate so that the RF path is completely isolated from the DC line. At the drain an inductor is used as the RF choke. The current rating for this inductor should be high enough to provide the required current at the operation conditions.

Bias Conditions

This evaluation board was optimized at a specific drain voltage, 7.5V. For different supply voltages, the matching circuits should be adjusted to fully utilize the device capability. The quiescent current is 40mA for the data shown below. The gain is higher at higher quiescent currents, particularly when the device is not completely saturated. For many communication systems, where the PA is never at idle state, a high quiescent current might be used.

PCB Material:

The PCB is Getek 28mil two layer board. The dielectric constant of Getek is 4.2.

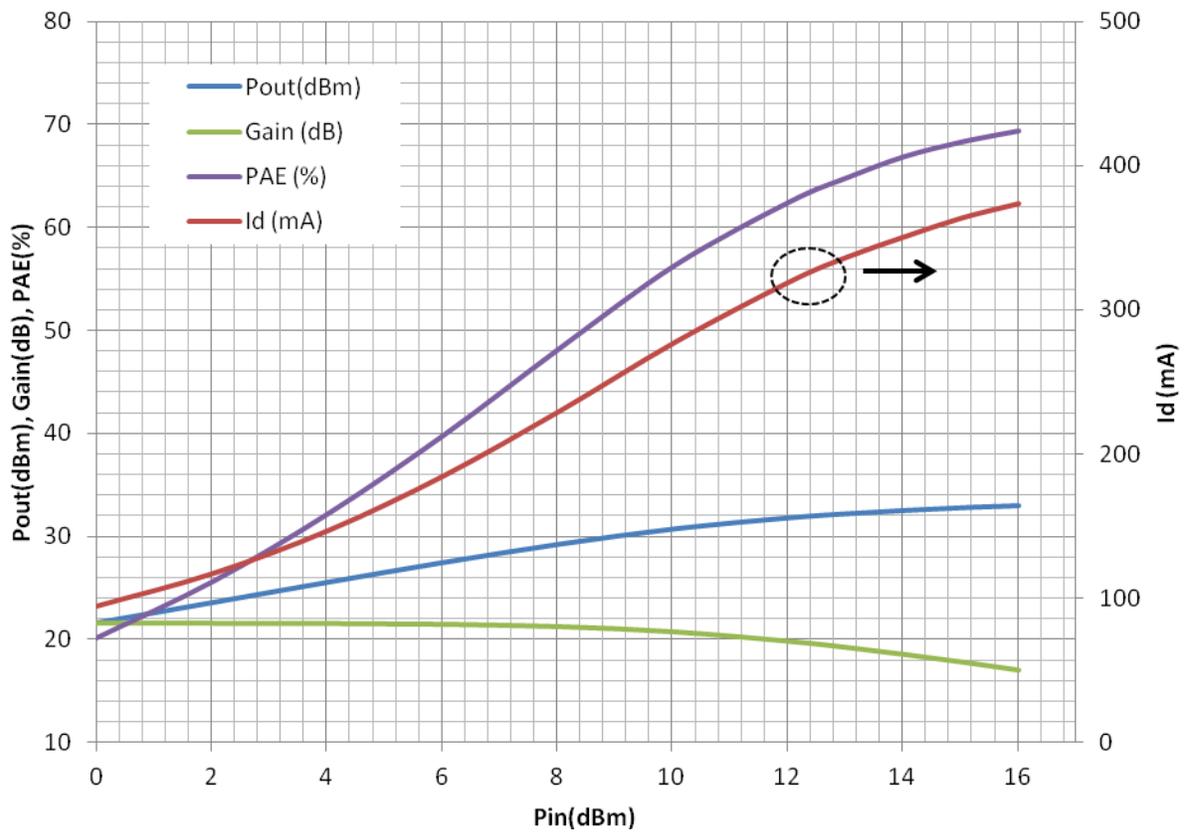
Typical Performance Data

Test Conditions:

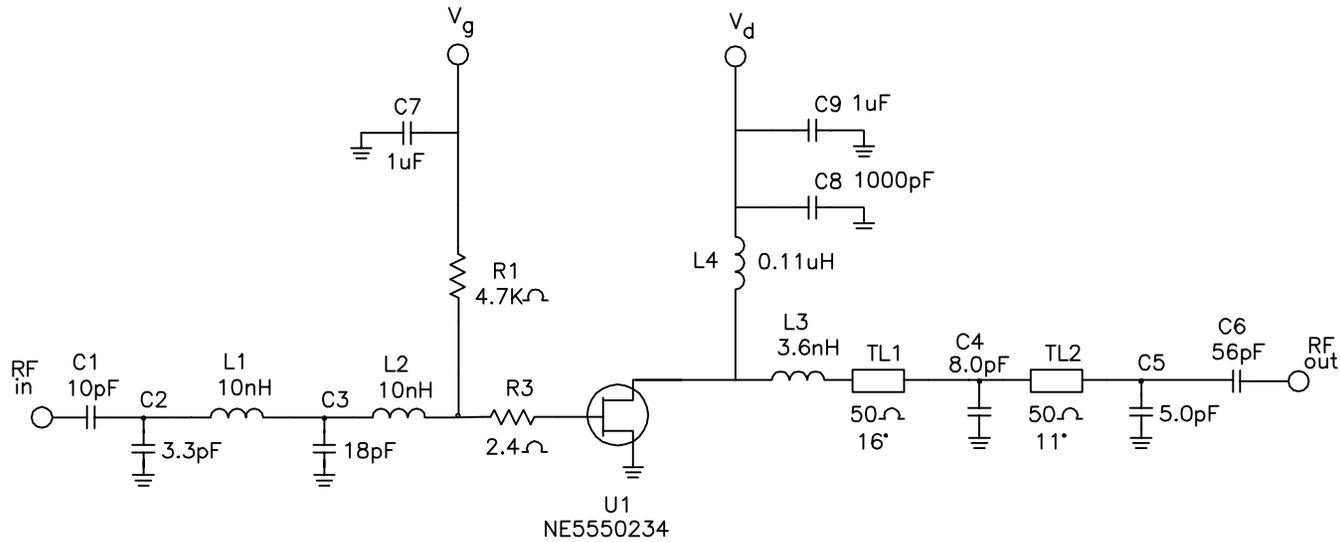
f=460MHz

Vd=7.5V, Idsq=40mA

Pout, Gain, PAE and Current vs Pin are shown in the following plot.



REVISIONS				
ZONE	LTR	DESCRIPTION	DATE	APPROVED



Note: All electrical lengths are at 460MHz

QTY	PART OR IDENTIFYING NO.	NOMENCLATURE OR DESCRIPTION	MATERIAL/SPECIFICATION	ITEM NO.
1	TF-101642		BLOCK	19
1	GRM1885C1H102JA01	C8	0603 1000pF CAP MURATA	18
2	GRM185R61C105KE44	C7,C9	0603 1uF CAP MURATA	17
1	GRM1885C1H560JA01	C6	0603 56pF CAP MURATA	16
1	GRM1885C1H5R0DZ01	C5	0603 5.0pF CAP MURATA	15
1	GRM1885C1H8R0DZ01	C4	0603 8.0pF CAP MURATA	14
1	GRM1885C1H180JA01	C3	0603 18pF CAP MURATA	13
1	GRM1885C1H3R3DZ01	C2	0603 3.3pF CAP MURATA	12
1	GRM1885C1H100JA01	C1	0603 10pF CAP MURATA	11
1	GENERIC	R3	0603 2.4 OHM RES	10
1	GENERIC	R2	0603 0 OHM RES	9
1	GENERIC	R1	0603 4.7 KOHM RES	8
1	0805AF-111XJR	L4	0805 0.11uH IND COILCRAFT	7
1	LQW18ANR47G00	L3	0603 3.6nH IND WIRE WOUND MURATA	6
2	LQG18HN10NJ00	L1,L2	0603 10nH IND MURATA	5
3	1205-003	P1, P2, P3	FEEDTHRU MURATA	4
2	142-0701-841	J1, J2	SMA FEMALE CONNECTOR E.F.JOHNSON	3
1	NE5550234	U1	IC RENESAS	2
1	CL-102046	PCB	COMPONENT LAYOUT DRAWING	1

PARTS LIST

UNLESS OTHERWISE SPECIFIED DIMENSIONS ARE IN INCHES TOLERANCES		APPROVALS		 4590 PATRICK HENRY DR. SANTA CLARA CA. 95054	
DECIMALS .XX± .01	ANGULAR ± 1°	Drawing by:	M Dong	8/16/2012	TITLE: NE5550234-EV04-A SCHEMATIC AND BOM
DO NOT SCALE DRAWING		Designed by:	M Dong	8/16/2012	
MATERIAL		Checked by:			
FINISH		Project Engineer:			SIZE: C FSCM NO.: DWG NO.: AD102065
NEXT ASSY	USED ON	Quality Control:			SCALE: NONE RELEASE DATE: PROTOTYPE: SHEET 1 OF 1
APPLICATION				REV: —	

